

Notice of References Cited	Application/Control No. 09/683,486		Applicant(s)/Patent Under Reexamination BRYANT ET AL.	
	Examiner Samuel A Gebremariam		Art Unit 2811	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-6,392,271	05-2002	Alavi et al.	257/328
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Hisamoto et al. (Finfet -A Self-aligned double gate mosfet scalable to 20nm), IEEE transactions on electron devices, vol. 47, no. 12, December 2000.
	V	Liu et al. (Fabrication of Fin-type Double gate mosfet structure by orientation-dependent etching and electron beam lithography)
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.